

REMARKS

Claims 1-13 are pending. Claims 1-11 are rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over U.S. Patent No. 6,194,762 to Yamazaki et al. ("Yamazaki"). Claims 8, 9 and 10 are rejected under 35 U.S.C. 102(e) as being anticipated by U.S. Patent 5,821,137 to Wakai et al. ("Wakai"). Claim 11 is rejected under 35 U.S.C. 103(a) as being unpatentable over Wakai in view of U.S. Patent 4,613,382 to Katayama et al. ("Katayama"). Claims 1-11 are amended, and claims 12 and 13 are added, by virtue of this Reply.

Regarding preliminary matters, Applicant thanks the Examiner for acknowledging Applicant's claim for foreign priority under 35 U.S.C. 119.

Regarding the rejection of claims 1-11 under the judicially created doctrine of obviousness-type double patenting as being unpatentable over Yamazaki, Applicant respectfully submits that the Terminal Disclaimer filed with this Reply pursuant to 37 CFR 3.73(b) and 37 CFR 1.321(c) is sufficient to overcome this rejection of claims 1-11. Therefore, Applicant requests that this rejection be withdrawn. Since no other rejection has been issued with respect to claims 1-7, Applicant submits that these claims, as well as new dependent claims 12 and 13 (each of which depend from one of claims 3 and 4), are now in condition for allowance, and such action is requested in the Examiner's next official communication.

Regarding the rejection of claims 8, 9 and 10 under 35 U.S.C. 102(e) as being anticipated by Wakai, amended claim 8 recites a "semiconductor device having at least one *p-channel* thin film transistor ... comprising ... a pair of portions containing n-type and p-type impurities (that) are formed adjacent to ... source and drain regions respectively (of the p-channel transistor), and wherein an electrode is connected to at least one of said pair of portions." Similarly, claim 9 recites a "semiconductor device having at least one *p-channel* thin film transistor ... comprising ... a pair of contact pads (that) are formed adjacent to ... source and drain regions respectively (of the p-channel transistor)." With regard to claim 9, Applicant notes that the claim limitation "contact pad(s)" finds support in the specification at, for example, page 13, line 30, as well as at page 5, line 30 – page 6, line 7.

Wakai, on the other hand, does not disclose or suggest such a p-channel thin film transistor, nor does the Office Action allege that Wakai provides such a teaching or suggestion.

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Rather, in paragraph 3 of the Office Action, FIG. 4E is referred to for a teaching of “a pair of portions containing n-type and p-type impurities (that) are formed adjacent to the source and drain regions respectively” of an n-channel transistor.

Based on the above, Applicant respectfully submits that independent claims 8 and 9, as well as dependent claims 10 and 11, are in condition for allowance, and such action is requested in the Examiner's next official communication.